Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D T_C = +25°C
-30V	9mΩ @ V_{GS} = -10V	-45A
	12mΩ @ V_{GS} = -4.5V	-35A

Description and Applications

This new generation 30V P-Channel Enhancement Mode MOSFET has been designed to minimize $R_{DS(ON)}$ and yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and loadswitch.

- Notebook Battery Power Management
- DC-DC Converters
- Loadswitch

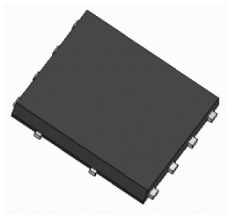
Features and Benefits

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- ESD HBM Protected up to 1kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

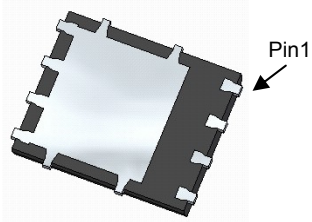
Mechanical Data

- Case: POWERDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.097 grams (approximate)

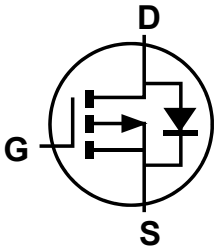
POWERDI5060-8



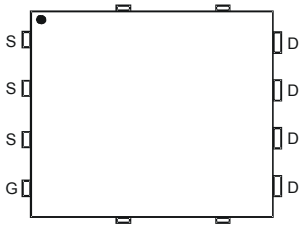
Top View



Bottom View



Internal Schematic



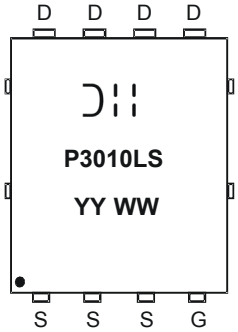
Top View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3012LPS-13	POWERDI5060-8	2500 / Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Ↄ¦¦ = Manufacturer's Marking
P3012LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 13 = 2013)
WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	13.2 10.5	A
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	11.4 9.1	A
Pulsed Drain Current (Notes 6)			I_{DM}	-100	A
Avalanche Current (Notes 7) L = 1mH			I_{AR}	-24	A
Avalanche Energy (Notes 7) L = 1mH			E_{AR}	292	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	1.29	W
Thermal Resistance, Junction to Ambient @ T_A = +25°C (Note 5)	$R_{\theta JA}$	97	°C/W
Power Dissipation (Note 6)	P_D	2.36	W
Thermal Resistance, Junction to Ambient @ T_A = +25°C (Note 6)	$R_{\theta JA}$	53	°C/W
Thermal Resistance, Junction to Case @ T_C = +25°C (Notes 6)	$R_{\theta JC}$	4.0	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.1	-1.6	-2.1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	7.5	9.0	mΩ	V_{GS} = -10V, I_D = -10A
		—	8.5	12.0		V_{GS} = -4.5V, I_D = -10A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	30	—	S	V_{DS} = -15V, I_D = -10A
Diode Forward Voltage	V_{SD}	—	-0.65	-1.0	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	6807	—	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	988	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	647	—	pF	
Gate Resistance	R_g	—	6.2	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -10V)	Q_g	—	139	—	nC	V_{DS} = -15V, I_D = -10A
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	66	—	nC	
Gate-Source Charge	Q_{gs}	—	19	—	nC	
Gate-Drain Charge	Q_{gd}	—	21	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	8.9	—	ns	V_{DS} = -15V, V_{GEN} = -10V, R_G = 6Ω, I_D = -1A
Turn-On Rise Time	t_r	—	10.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	254	—	ns	
Turn-Off Fall Time	t_f	—	95	—	ns	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = 25°C
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

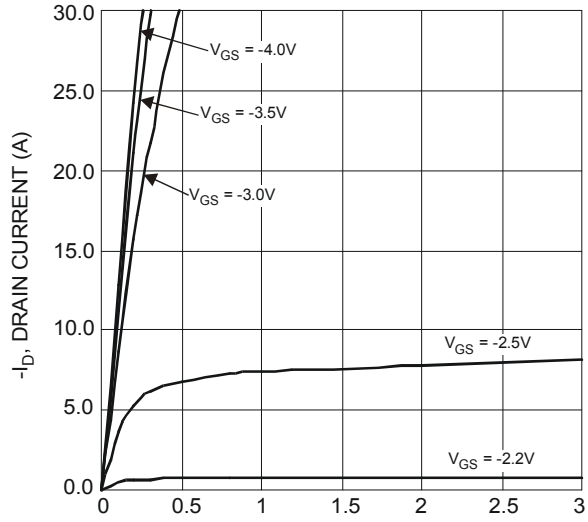


Figure 1 Typical Output Characteristics

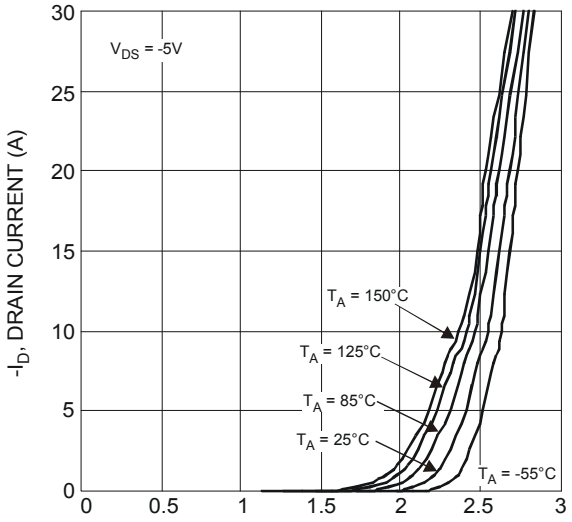


Figure 2 Typical Transfer Characteristics

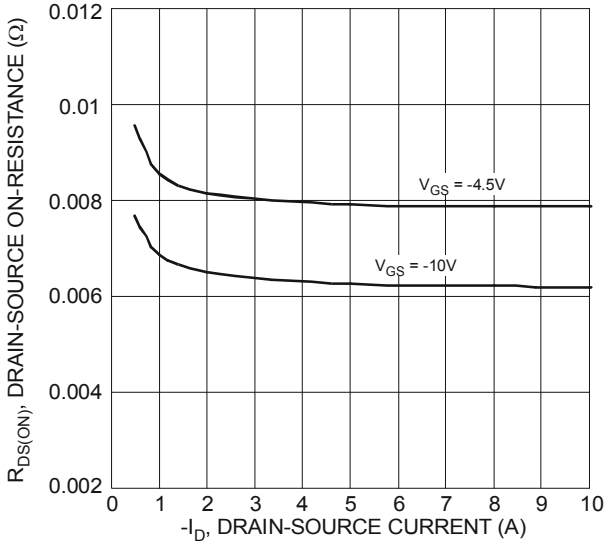


Figure 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

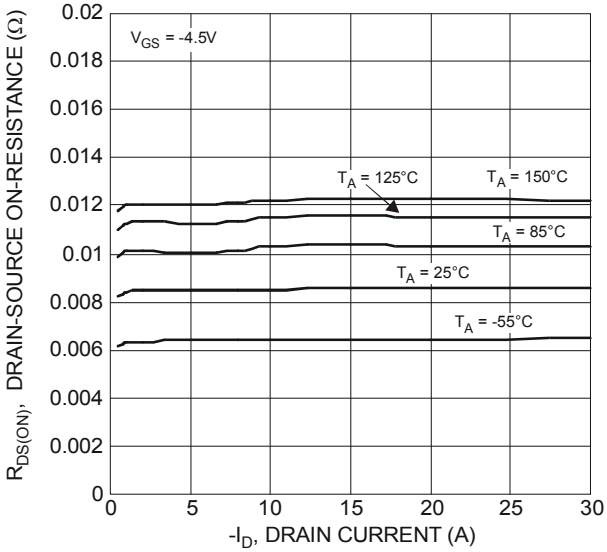


Figure 4 Typical On-Resistance
vs. Drain Current and Temperature

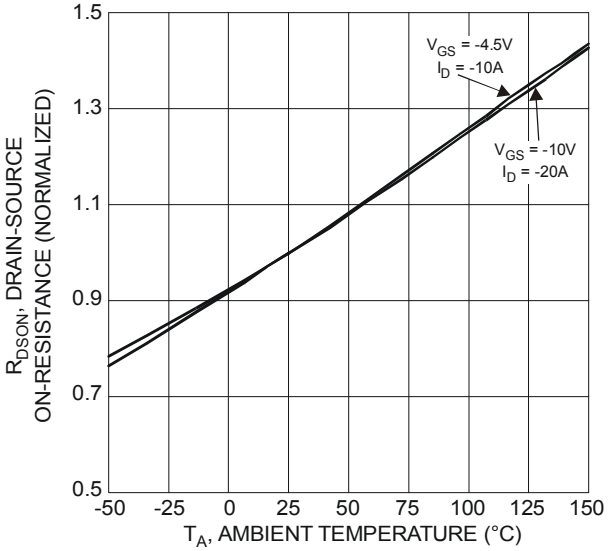


Figure 5 On-Resistance Variation with Temperature

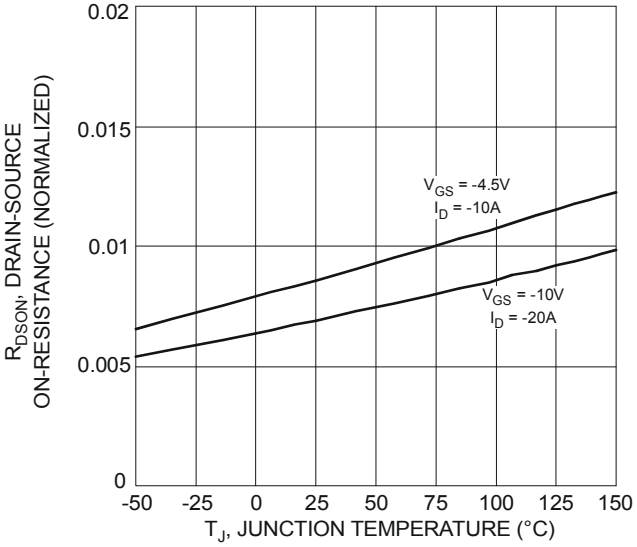


Figure 6 On-Resistance Variation with Temperature

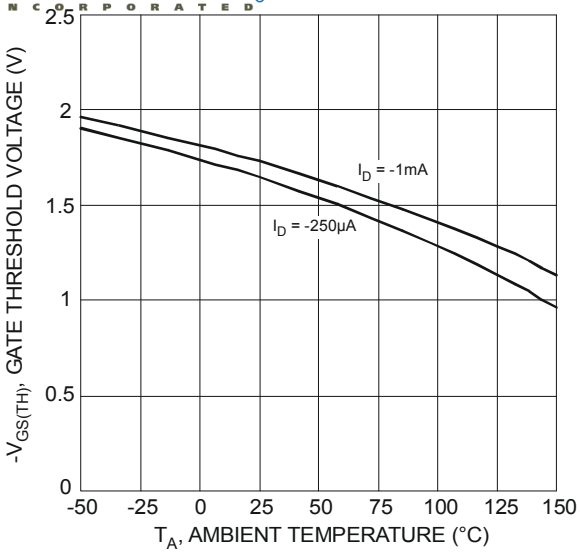


Figure 7 Gate Threshold Variation vs. Ambient Temperature

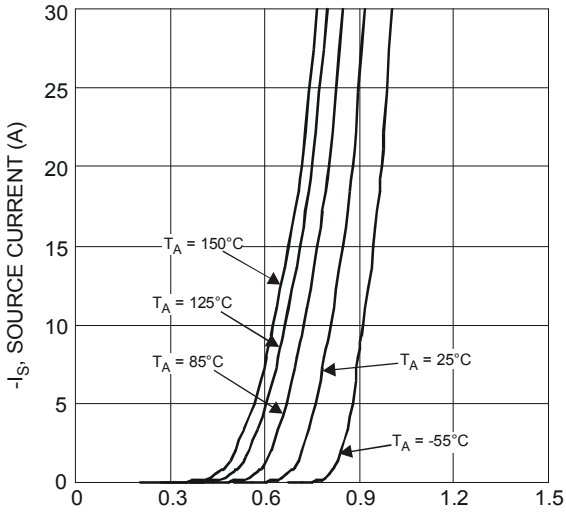


Figure 8 Diode Forward Voltage vs. Current

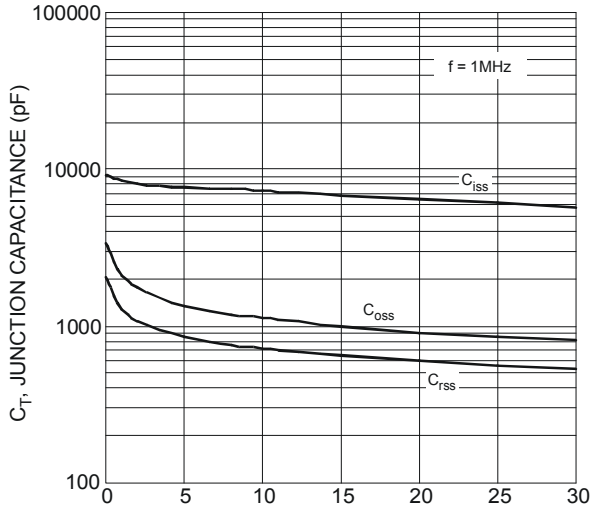


Figure 9 Typical Total Capacitance

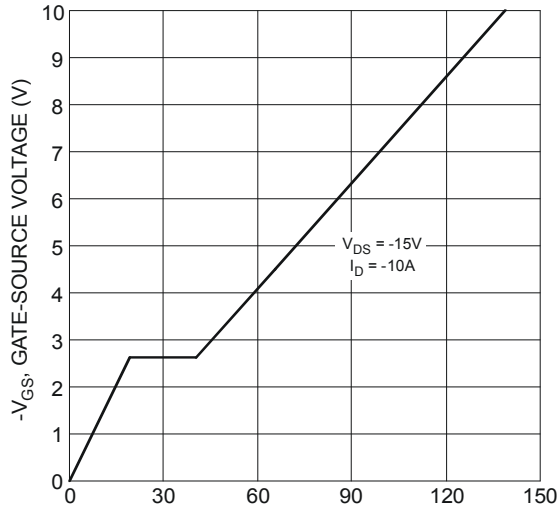


Figure 10 Gate-Source Voltage vs. Total Gate Charge

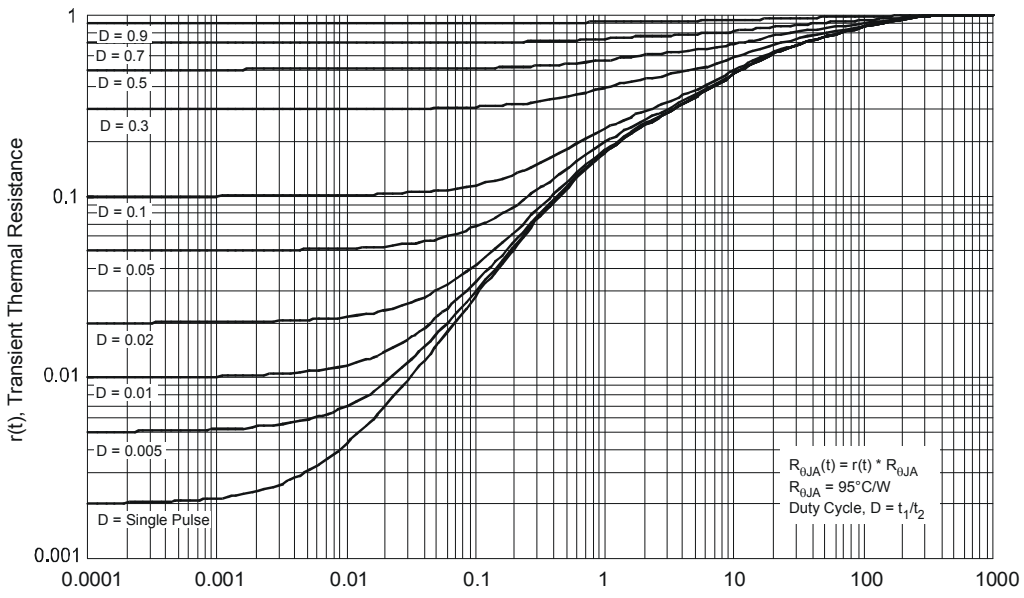
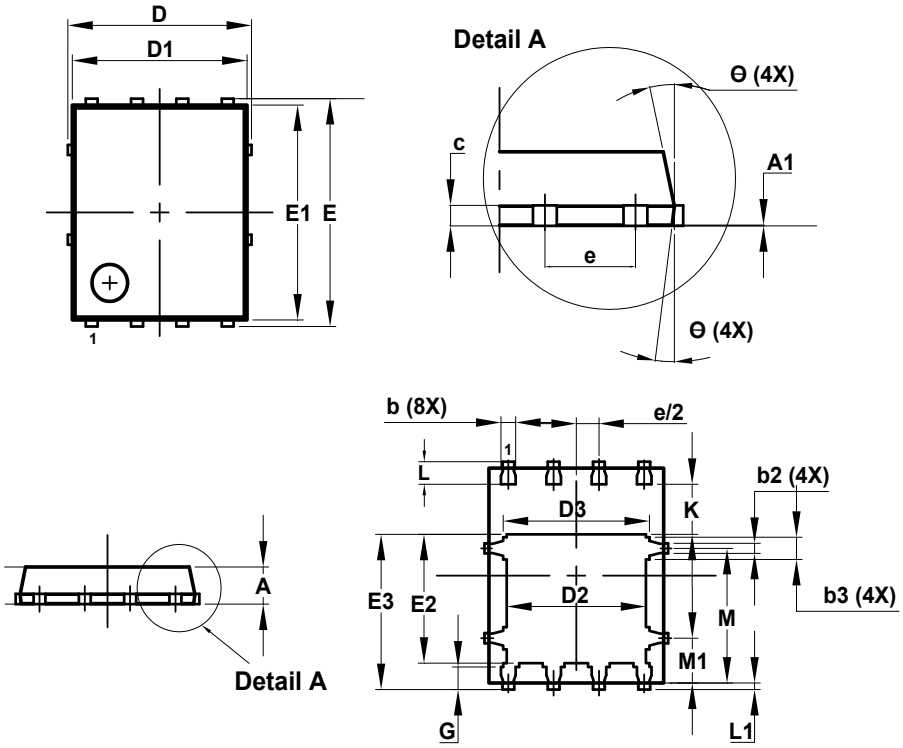


Figure 11 Transient Thermal Response

Package Outline Dimensions

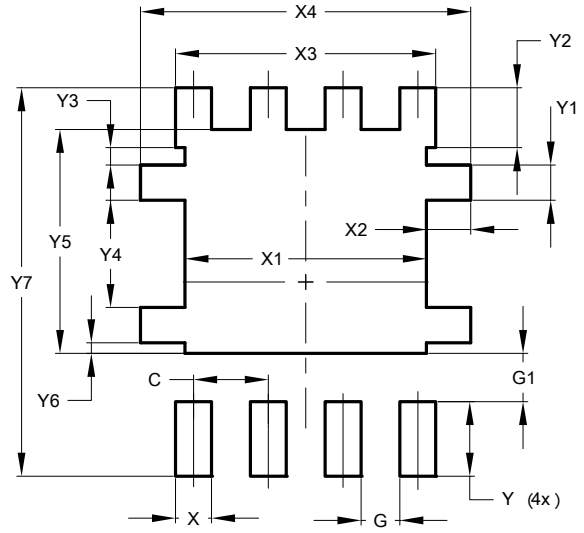
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	–
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	–	–
L	0.51	0.71	0.61
L1	0.10	0.20	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
Θ	10°	12°	11°
Θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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